

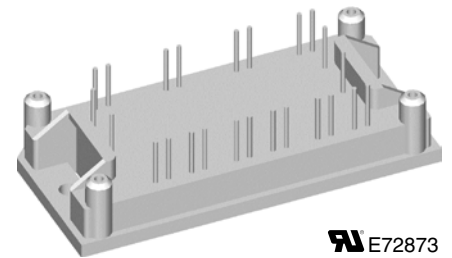
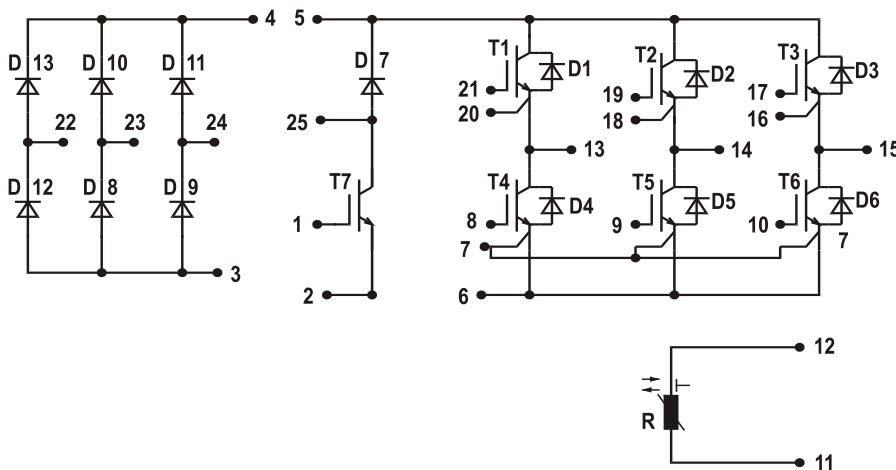
# Converter - Brake - Inverter Module (CBI 1) NPT IGBT

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 600 \text{ V}$	$V_{CES} = 600 \text{ V}$
$I_{DAVM25} = 130 \text{ A}$	$I_{C25} = 25 \text{ A}$	$I_{C25} = 42 \text{ A}$
$I_{FSM} = 320 \text{ A}$	$V_{CE(sat)} = 2.0 \text{ V}$	$V_{CE(sat)} = 2.3 \text{ V}$

Preliminary data

**Part name** (Marking on product)

MUBW35-06A6K



E72873

Pin configuration see outlines.

**Features:**

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT IGBTs
- low saturation voltage
- positive temperature coefficient
- fast switching
- short tail current
- Epitaxial free wheeling diodes with hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

**Application:**

- AC motor drives with
- Input from single or three phase grid
  - Three phase synchronous or asynchronous motor
  - Electric braking operation

**Package:**

- UL registered
- Industry standard E1-pack

**Output Inverter T1 - T6**

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
$V_{CES}$	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$			600	V	
$V_{GES}$	max. DC gate voltage	continuous			$\pm 20$	V	
$V_{GEM}$	max. transient collector gate voltage	transient			$\pm 30$	V	
$I_{C25}$	collector current	$T_C = 25^{\circ}\text{C}$			42	A	
$I_{C80}$		$T_C = 80^{\circ}\text{C}$			29	A	
$P_{tot}$	total power dissipation	$T_C = 25^{\circ}\text{C}$			130	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 35\text{ A}; V_{GE} = 15\text{ V}$			2.3 2.6	V V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.7\text{ mA}; V_{GE} = V_{CE}$	4.5		6.5	V	
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			1.5	0.75 mA mA	
$I_{GES}$	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			200	nA	
$C_{ies}$	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$			1600	pF	
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 30\text{ A}$			95	nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 30\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 33\ \Omega$			50	ns	
$t_r$	current rise time		$T_{VJ} = 125^{\circ}\text{C}$			50	ns
$t_{d(off)}$	turn-off delay time					270	ns
$t_f$	current fall time					40	ns
$E_{on}$	turn-on energy per pulse					1.4	mJ
$E_{off}$	turn-off energy per pulse					1.0	mJ
$I_{CM}$	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 33\ \Omega$ $L = 100\ \mu\text{H};$ clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$			60	A	
$t_{SC}$ (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 82\ \Omega;$ non-repetitive			10	$\mu\text{s}$	
$R_{thJC}$	thermal resistance junction to case	(per IGBT)			0.95	K/W	
$R_{thCH}$	thermal resistance case to heatsink	(per IGBT)			0.35	K/W	

**Output Inverter D1 - D6**

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
$V_{RRM}$	max. repetitive reverse voltage	$T_{VJ} = 150^{\circ}\text{C}$			600	V	
$I_{F25}$	forward current	$T_C = 25^{\circ}\text{C}$			69	A	
$I_{F80}$		$T_C = 80^{\circ}\text{C}$			46	A	
$V_F$	forward voltage	$I_F = 35\text{ A}; V_{GE} = 0\text{ V}$			1.2	1.7 V V	
$I_{RM}$	max. reverse recovery current	$V_R = 100\text{ V}$ $di_f/dt = -100\text{ A}/\mu\text{s}$ $I_F = 50\text{ A}; V_{GE} = 0\text{ V}$			5	A	
$t_{rr}$	reverse recovery time		$T_{VJ} = 100^{\circ}\text{C}$			100	ns
$E_{rec(off)}$	reverse recovery energy					tbid	$\mu\text{J}$
$R_{thJC}$	thermal resistance junction to case	(per diode)			0.9	K/W	
$R_{thCH}$	thermal resistance case to heatsink	(per diode)			0.3	K/W	

 $T_C = 25^{\circ}\text{C}$  unless otherwise stated

**Brake Chopper T7**

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
$V_{CES}$	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$			600	V
$V_{GES}$	max. DC gate voltage	continuous			$\pm 20$	V
$V_{GEM}$	max. transient collector gate voltage	transient			$\pm 30$	V
$I_{C25}$	collector current	$T_C = 25^{\circ}\text{C}$			25	A
$I_{C80}$		$T_C = 80^{\circ}\text{C}$			17	A
$P_{tot}$	total power dissipation	$T_C = 25^{\circ}\text{C}$			80	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 15\text{ A}; V_{GE} = 15\text{ V}$			2.0 2.3	V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.4\text{ mA}; V_{GE} = V_{CE}$	4.5		6.5	V
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			0.8	mA mA
$I_{GES}$	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			100	nA
$C_{ies}$	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$			800	pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 15\text{ A}$			57	nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 15\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 68\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$		30	ns
$t_r$	current rise time				50	ns
$t_{d(off)}$	turn-off delay time				270	ns
$t_f$	current fall time				40	ns
$E_{on}$	turn-on energy per pulse				0.7	mJ
$E_{off}$	turn-off energy per pulse				0.5	mJ
$I_{CM}$	reverse bias safe operating area	$RBSOA; V_{GE} = \pm 15\text{ V}; R_G = 68\ \Omega$ $L = 100\ \mu\text{H};$ clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$		30	A
$t_{SC}$ (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 82\ \Omega;$ non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$		10	$\mu\text{s}$
$R_{thJC}$	thermal resistance junction to case	(per IGBT)			1.55	K/W
$R_{thCH}$	thermal resistance case to heatsink	(per IGBT)			0.5	K/W

**Brake Chopper D7**

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
$V_{RRM}$	max. repetitive reverse voltage	$T_{VJ} = 150^{\circ}\text{C}$			600	V
$I_{F25}$	forward current	$T_C = 25^{\circ}\text{C}$			21	A
$I_{F80}$		$T_C = 80^{\circ}\text{C}$			14	A
$V_F$	forward voltage	$I_F = 15\text{ A}; V_{GE} = 0\text{ V}$			2.3	V
					1.5	V
$I_R$	reverse current	$V_R = V_{RRM}$			0.06	mA mA
					0.2	
$I_{RM}$	max. reverse recovery current	$V_R = 100\text{ V}; I_F = 12\text{ A}$ $di_F/dt = -100\text{ A}/\mu\text{s}$	$T_{VJ} = 100^{\circ}\text{C}$		3.5	A
$t_{rr}$	reverse recovery time				80	ns
$R_{thJC}$	thermal resistance junction to case	(per diode)			2.5	K/W
$R_{thCH}$	thermal resistance case to heatsink	(per diode)			0.85	K/W

 $T_C = 25^{\circ}\text{C}$  unless otherwise stated

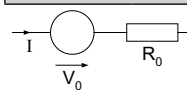
Input Rectifier Bridge D8 - D13					
Symbol	Definitions	Conditions			Maximum Ratings
$V_{RRM}$	max. repetitive reverse voltage				1600 V
$I_{FAV}$	average forward current	sine 180°	$T_C = 80^\circ\text{C}$	31	A
$I_{DAVM}$	max. average DC output current	rectangular; $d = 1/3$ ; bridge	$T_C = 80^\circ\text{C}$	89	A
$I_{FSM}$	max. surge forward current	$t = 10$ ms; sine 50 Hz	$T_C = 25^\circ\text{C}$	320	A
$P_{tot}$	total power dissipation	$T_C = 25^\circ\text{C}$			80 W

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
$V_F$	forward voltage	$I_F = 30$ A	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	1.0 1.1	1.35 V
$I_R$	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.4	0.02 mA mA
$R_{thJC}$	thermal resistance junction to case	(per diode)	$T_{VJ} = 25^\circ\text{C}$		1.4 K/W
$R_{thCH}$	thermal resistance case to heatsink	(per diode)		0.45	K/W

Temperature Sensor NTC							
Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
$R_{25}$	resistance		$T_C = 25^\circ\text{C}$	4.45	4.7	5.0	k $\Omega$
$B_{25/85}$					3510		K

Module						
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
$T_{VJ}$	operating temperature		-40		125	$^\circ\text{C}$
$T_{VJM}$	max. virtual junction temperature				150	$^\circ\text{C}$
$T_{stg}$	storage temperature		-40		125	$^\circ\text{C}$
$V_{ISOL}$	isolation voltage	$I_{ISOL} \leq 1$ mA; 50/60 Hz			2500	V~
$M_d$	mounting torque	(M4)	2.0		2.2	Nm
$d_S$	creep distance on surface		12.7			mm
$d_A$	strike distance through air		12.7			mm
<b>Weight</b>				40		g

### Equivalent Circuits for Simulation



Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
$V_0$	rectifier diode	D8 - D13	$T_{VJ} = 125^\circ\text{C}$	0.90		V
$R_0$				9		m $\Omega$
$V_0$	IGBT	T1 - T6	$T_{VJ} = 125^\circ\text{C}$	1.0		V
$R_0$				4		m $\Omega$
$V_0$	free wheeling diode	D1 - D6	$T_{VJ} = 125^\circ\text{C}$	1.05		V
$R_0$				7		m $\Omega$
$V_0$	IGBT	T7	$T_{VJ} = 125^\circ\text{C}$	1.0		V
$R_0$				70		m $\Omega$
$V_0$	free wheeling diode	D7	$T_{VJ} = 125^\circ\text{C}$	1.25		V
$R_0$				26		m $\Omega$

$T_C = 25^\circ\text{C}$  unless otherwise stated





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- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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